

TOSHIBA FIELD EFFECT TRANSISTOR
SILICON P CHANNEL MOS TYPE
2SJ115**TOSHIBA (DISCRETE/OPTO)**

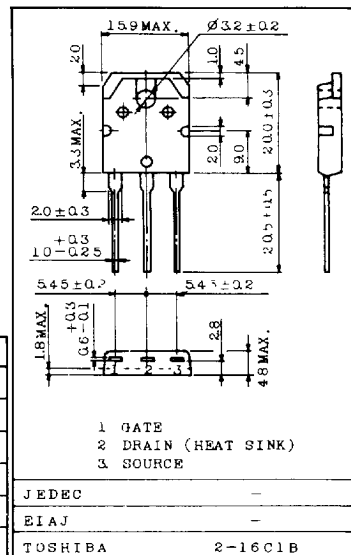
AUDIO FREQUENCY POWER AMPLIFIER APPLICATION.

FEATURES:

- High Breakdown Voltage : $V_{DS} = -160V$
- High Forward Transfer Admittance : $|Y_{fs}| = 2.0S$ (Typ.)
- Complementary to 2SK405

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	-160	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	-8	A
Power Dissipation ($T_c = 25^\circ C$)	P_D	100	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

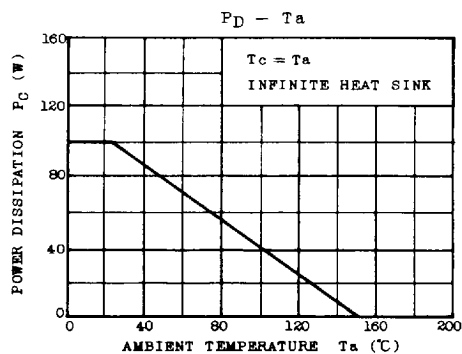
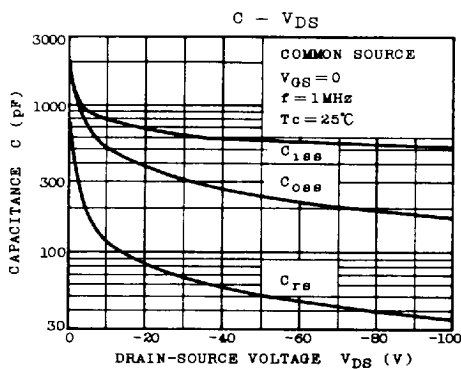
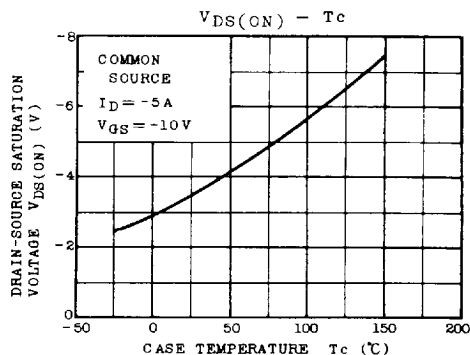
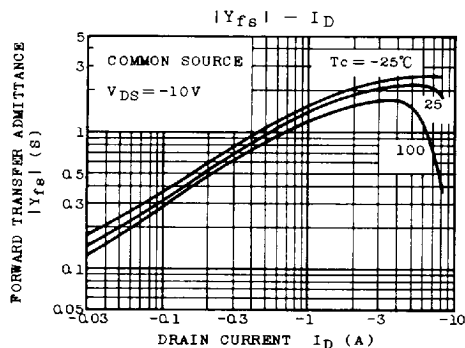
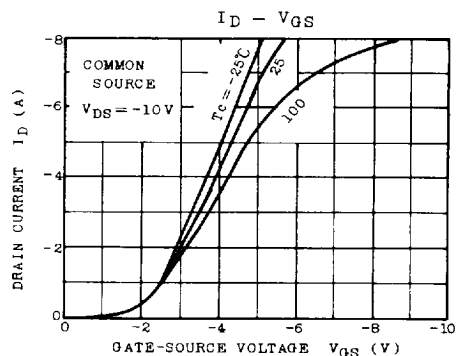
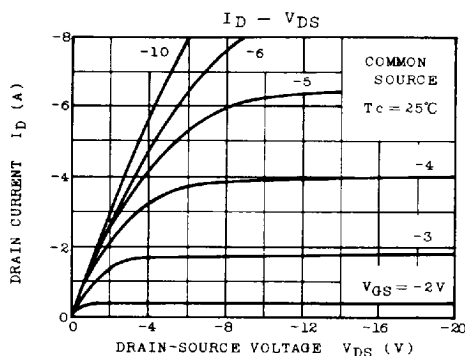


Weight : 4.6g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{DS} = 0, V_{GS} = \pm 20V$	-	-	± 1.0	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -5mA, V_{GS} = 0$	-160	-	-	V
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$ (Note)	$V_{DS} = -10V, I_D = -0.1A$	-0.8	-	-2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D = -5A, V_{GS} = -10V$	-	-3.5	-7.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -2A$	1.0	2.0	-	S
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	-	800	-	pF
Output Capacitance	C_{oss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	-	500	-	pF
Reverse Transfer Capacitance	C_{rs}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	-	110	-	pF

Note : $V_{GS(OFF)}$ Classification 0 : $-0.8 \sim -1.6$, Y : $-1.4 \sim -2.8$



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